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# Quasi-Resonant Controllers with Integrated Power MOSFET STR-Y6700 Series

#### **General Descriptions**

The STR-Y6700 series are power ICs for switching power supplies, incorporating a MOSFET and a quasi-resonant controller IC.

Including an auto standby function in the controller, the product achieves the low standby power by the automatic switching between the PWM operation in normal operation, one bottom-skip operation under medium to light load conditions and the burst-oscillation under light load conditions.

The product achieves high cost-performance power supply systems with few external components.

#### Features

• Multi-mode Control

The optimum operation depending on load conditions is changed automatically and is achieved high efficiency operation across the full range of loads.

**Operation Mode** 

| Normal load          | Quasi-resonant mode     |
|----------------------|-------------------------|
| Medium to light load | One bottom-skip mode    |
| Light load           | Burst oscillation mode  |
|                      | (Auto standby function) |

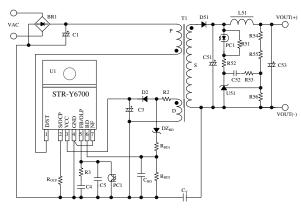
- No load power consumption  $P_{IN} \le 30 \text{ mW} (100 \text{VAC})$  $P_{IN} \le 50 \text{ mW} (230 \text{VAC})$
- Leading Edge Blanking Function
- Bias Assist Function
- Built-in startup circuit reduces
- Protections

Overcurrent Protection 1 (OCP1): Pulse-by-Pulse, with Input Compensation Function

Overcurrent Protection 2 (OCP2)<sup>(1)</sup>: Latched shutdown Overload Protection (OLP): Latched shutdown Overvoltage Protection (OVP): Latched shutdown Thermal Shutdown Protection (TSD): Latched shutdown

<sup>(1)</sup> Products with the last letter "A" don't have the OCP2 function.

# **Typical Application**



# Package

TO220F-7L



Not to Scale

# Lineup

• Electrical Characteristics

| Products                | V <sub>DSS</sub> (min.) | R <sub>DS(ON)</sub> (max.) |
|-------------------------|-------------------------|----------------------------|
| STR-Y6735<br>STR-Y6735A | 500 V                   | 0.8 Ω                      |
| STR-Y6753               | 650 V                   | 1.9 Ω                      |
| STR-Y6754               | 030 V                   | 1.4 Ω                      |
| STR-Y6766<br>STR-Y6766A |                         | 1.7 Ω                      |
| STR-Y6765               | 800 V                   | 2.2 Ω                      |
| STR-Y6763<br>STR-Y6763A |                         | 3.5 Ω                      |

• Output Power,  $P_{OUT}^{(2)}$ 

| Products                | P <sub>OUT</sub> (Op | P <sub>OUT</sub> (Open frame) |  |  |  |  |
|-------------------------|----------------------|-------------------------------|--|--|--|--|
| Products                | 380VDC               | 85~265VAC                     |  |  |  |  |
| STR-Y6735<br>STR-Y6735A | 120 W(100VAC)        | _                             |  |  |  |  |
| STR-Y6753               | 100 W                | 60 W                          |  |  |  |  |
| STR-Y6754               | 120 W                | 67 W                          |  |  |  |  |
| STR-Y6766<br>STR-Y6766A | 140 W                | 80 W                          |  |  |  |  |
| STR-Y6765               | 120 W                | 70 W                          |  |  |  |  |
| STR-Y6763<br>STR-Y6763A | 80 W                 | 50 W                          |  |  |  |  |

(2) The output power is actual continues power that is measured at 50 °C ambient. The peak output power can be 120 to 140 % of the value stated here. Core size, ON Duty, and thermal design affect the output power. It may be less than the value stated here.

# Applications

- White goods
- Office automation equipment
- Industrial equipment

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#### **Absolute Maximum Ratings** 1.

• Current polarities are defined as follows: a current flow going into the IC (sinking) is positive current (+); and a current flow coming out of the IC (sourcing) is negative current (-).

| • Unless otherwise specified $T_A = 25 \text{ °C}$ |  |
|--|--|
|--|--|

| Parameter   | Symbol               | Test Conditions                  | Pins  | Rating              | Units | Notes                        |
|---|----------------------|----------------------------------|-------|---------------------|-------|------------------------------|
|   |                      |                                  |       | 6.7                 |       | STR-Y6763 / 63A              |
|   |                      | Single pulse                     |       | 8.9                 |       | STR-Y6765                    |
| Drain Peak Current <sup>(1)</sup>   | т                    |                                  | 1 2   | 9.2                 |       | STR-Y6753                    |
| Drain Peak Current  | I <sub>DPEAK</sub>   |                                  | 1 – 2 | 10.5                | А     | STR-Y6766 / 66A              |
|   |                      |                                  |       | 11.0                |       | STR-Y6754                    |
|   |                      |                                  |       | 14.6                |       | STR-Y6735 / 35A              |
|   |                      |                                  |       | 6.7                 |       | STR-Y6763 / 63A              |
|   |                      |                                  |       | 8.9                 |       | STR-Y6765                    |
| Maximum Societation - $C_{\rm constant}^{(2)}$  | т                    | Single pulse                     | 1 2   | 9.2                 |       | STR-Y6753                    |
| Maximum Switching Current <sup>(2)</sup>  | I <sub>DMAX</sub>    | $Ta = -20$ to $125^{\circ}C$     | 1 – 2 | 10.5                | A     | STR-Y6766 / 66A              |
|   |                      |                                  |       | 11.0                |       | STR-Y6754                    |
|   |                      |                                  |       | 14.6                |       | STR-Y6735 / 35A              |
|   |                      | I <sub>LPEAK</sub> =2.3A         |       | 60                  |       | STR-Y6763 / 63A              |
|   |                      | I <sub>LPEAK</sub> =2.6A         |       | 77                  | mJ    | STR-Y6765                    |
| $\mathbf{A} = 1 + $ | E <sub>AS</sub>      | I <sub>LPEAK</sub> =2.9A         | 1 0   | 99                  |       | STR-Y6753                    |
| Avalanche Energy <sup>(3)(4)</sup>  |                      | I <sub>LPEAK</sub> =3.2A         | 1 – 2 | 116                 |       | STR-Y6766 / 66A              |
|   |                      | I <sub>LPEAK</sub> =4.1A         |       | 198                 |       | STR-Y6754                    |
|   |                      | I <sub>LPEAK</sub> =3.5A         |       | 152                 |       | STR-Y6735 / 35A              |
| D/ST Pin Voltage  | V <sub>STARTUP</sub> |                                  | 1 – 4 | $-1.0$ to $V_{DSS}$ | V     |                              |
| S/OCP Pin Voltage   | V <sub>OCP</sub>     |                                  | 2 - 4 | - 2.0 to 6.0        | V     |                              |
| VCC Pin Voltage   | V <sub>CC</sub>      |                                  | 3 – 4 | 35                  | V     |                              |
| FB/OLP Pin Voltage  | $V_{FB}$             |                                  | 5 – 4 | - 0.3 to 7.0        | V     |                              |
| FB/OLP Pin Sink Current   | $I_{FB}$             |                                  | 5 - 4 | 10.0                | mA    |                              |
| BD Pin Voltage  | $V_{BD}$             |                                  | 6 – 4 | - 6.0 to 6.0        | V     |                              |
|   |                      |                                  |       | 19.9                |       | STR-Y6763 / 63A              |
|   |                      |                                  | 1 – 2 | 21.8                |       | STR-Y6765                    |
| (5)   |                      | With infinite                    |       | 20.2                | W     | STR-Y6753                    |
| Power Dissipation <sup>(5)</sup>  | $P_{D1}$             | heatsink                         |       | 23.6                |       | STR-Y6766 / 66A              |
|   |                      |                                  |       | 21.5                |       | STR-Y6735 / 35A<br>STR-Y6754 |
|   |                      | Without heatsink                 | 1 – 2 | 1.8                 | W     |                              |
| Control Part Power Dissipation  | P <sub>D2</sub>      | V <sub>CC</sub> ×I <sub>CC</sub> | 3 – 4 | 0.8                 | W     |                              |
| Internal Frame Temperature in Operation   | $T_{\rm F}$          |                                  |       | - 20 to 115         | °C    |                              |
| Operating Ambient Temperature   | T <sub>OP</sub>      |                                  | -     | - 20 to 115         | °C    |                              |
| Storage Temperature   | T <sub>stg</sub>     |                                  | -     | - 40 to 125         | °C    |                              |
| Junction Temperature  | $T_{ch}$             |                                  |       | 150                 | °C    |                              |

 <sup>(1)</sup> Refer to 3.3 MOSFET Safe Operating Area Curves
 <sup>(2)</sup> The maximum switching current is the drain current determined by the drive voltage of the IC and threshold voltage  $(V_{th})$  of the MOSFET.

<sup>(3)</sup> Refer to Figure 3-2 Avalanche Energy Derating Coefficient Curve

<sup>(4)</sup> Single pulse,  $V_{DD} = 99$  V, L = 20 mH

 $^{(5)}$  Refer to 3.2 T<sub>A</sub>-P<sub>D1</sub>curves.

#### 2. **Electrical Characteristics**

- The polarity value for current specifies a sink as "+," and a source as "-," referencing the IC.
- Unless otherwise specified,  $T_A = 25 \text{ °C}$ ,  $V_{CC} = 20 \text{ V}$

| Parameter   | Symbol                   | Test<br>Conditions | Pins  | Min.  | Тур.  | Max.  | Units | Notes   |
|---|--------------------------|--------------------|-------|-------|-------|-------|-------|---|
| Power Supply Startup Operati  | on                       |                    |       |       |       |       |       |   |
| Operation Start Voltage   | V <sub>CC(ON)</sub>      |                    | 3 - 4 | 13.8  | 15.1  | 17.3  | V     |   |
| Operation Stop Voltage <sup>(1)</sup>   | V <sub>CC(OFF)</sub>     |                    | 3 - 4 | 8.4   | 9.4   | 10.7  | V     |   |
| Circuit Current in Operation  | I <sub>CC(ON)</sub>      |                    | 3 - 4 | _     | 1.3   | 3.7   | mA    |   |
| Circuit Current in<br>Non-Operation   | I <sub>CC(OFF)</sub>     | $V_{CC} = 13 V$    | 3 - 4 | _     | 4.5   | 50    | μA    |   |
| Startup Circuit Operation<br>Voltage  | V <sub>START(ON)</sub>   |                    | 1 – 4 | 42    | 57    | 72    | V     |   |
| Startup Current   | I <sub>CC(STARTUP)</sub> | $V_{CC} = 13 V$    | 3 - 4 | - 4.5 | - 3.1 | - 1.0 | mA    |   |
| Startup Current Biasing<br>Threshold Voltage                                    | V <sub>CC(BIAS)</sub>    |                    | 3 - 4 | 9.5   | 11.0  | 12.5  | V     |   |
| PWM Switching Frequency   | f <sub>OSC</sub>         |                    | 1 – 4 | 18.4  | 21.0  | 24.4  | kHz   |   |
| Soft Start Operation Duration   | t <sub>ss</sub>          |                    | 1 – 4 | -     | 6.05  | Ι     | ms    |   |
| Normal Operation  | ·                        |                    |       |       |       |       |       |   |
| Bottom-Skip Operation<br>Threshold Voltage 1                                    | V <sub>OCP(BS1)</sub>    |                    | 2-4   | 0.487 | 0.572 | 0.665 | V     |   |
| Bottom-Skip Operation<br>Threshold Voltage 2                                    | V <sub>OCP(BS2)</sub>    |                    | 2-4   | 0.200 | 0.289 | 0.380 | V     |   |
| Quasi-Resonant Operation<br>Threshold Voltage 1                                 | V <sub>BD(TH1)</sub>     |                    | 6 - 4 | 0.14  | 0.24  | 0.34  | V     |   |
| Quasi-Resonant Operation<br>Threshold Voltage 2 <sup>(2)</sup>                  | V <sub>BD(TH2)</sub>     |                    | 6 - 4 | 0.07  | 0.17  | 0.27  | V     |   |
| Maximum Feedback Current  | I <sub>FB(MAX)</sub>     |                    | 5 - 4 | -320  | -205  | -120  | μA    |   |
| Standby Operation   |                          |                    |       |       |       |       |       |   |
| Standby Operation Threshold Voltage   | V <sub>FB(STBOP)</sub>   |                    | 5 - 4 | 0.45  | 0.80  | 1.15  | V     |   |
| Protected Operation   |                          |                    |       |       |       |       |       |   |
| Maximum On-Time   | t <sub>ON(MAX)</sub>     |                    | 1 – 4 | 30.0  | 40.0  | 50.0  | μs    |   |
| Leading Edge Blanking Time  | t <sub>ON(LEB)</sub>     |                    | 1 – 4 | _     | 455   | _     | ns    | STR-Y6735<br>/ 35A/ 65/<br>66/ 54             |
| Deading Dage Dialiking Time   | CON(LEB)                 |                    | 1 1   | _     | 470   | _     | 115   | STR-Y6763<br>/ 63A/ 53                        |
| Overcurrent Detection 1<br>Threshold Voltage in Input<br>Compensation Operation | V <sub>OCP(L)</sub>      | $V_{BD} = -3V$     | 2-4   | 0.560 | 0.660 | 0.760 | V     |   |
| Overcurrent Detection 1<br>Threshold Voltage in Normal<br>Operation             | V <sub>OCP(H)</sub>      | $V_{BD} = 0V$      | 2-4   | 0.820 | 0.910 | 1.000 | V     |   |
| Overcurrent Detection 2<br>Threshold Voltage                                    | V <sub>OCP(La.OFF)</sub> |                    | 2-4   | 1.65  | 1.83  | 2.01  | V     | Products<br>without the<br>last letter<br>"A" |

| Parameter  | Symbol                      | Test<br>Conditions                | Pins  | Min.            | Тур. | Max. | Units                   | Notes                                      |           |           |
|--|-----------------------------|-----------------------------------|-------|-----------------|------|------|-------------------------|--|-----------|-----------|
| BD Pin Source Current                              | I <sub>BD(O)</sub>          |                                   | 6 - 4 | - 250           | - 83 | - 30 | μA                      |  |           |           |
| OLP Bias Current                                   | I <sub>FB(OLP)</sub>        |                                   | 5-4   | - 15            | - 10 | - 5  | μA                      |  |           |           |
| OLP Threshold Voltage                              | V <sub>FB(OLP)</sub>        |                                   | 5 - 4 | 5.50            | 5.96 | 6.40 | V                       |  |           |           |
| FB Pin Maximum Voltage in<br>Feedback Operation    | V <sub>FB(MAX)</sub>        |                                   | 5 - 4 | 3.70            | 4.05 | 4.40 | v                       |  |           |           |
| OVP Threshold Voltage                              | V <sub>CC(OVP)</sub>        |                                   | 3-4   | 28.5            | 31.5 | 34.0 | V                       |  |           |           |
| Thermal Shutdown Operating<br>Temperature          | $T_{j(TSD)}$                |                                   | _     | 135             | -    | -    | °C                      |  |           |           |
| MOSFET   |                             |                                   |       |                 |      |      | -                       |  |           |           |
|  |                             |                                   |       | 500             | -    | -    |                         | STR-Y6735 /<br>35A                         |           |           |
| Drain-to-Source Breakdown<br>Voltage               | V <sub>DSS</sub>            | I <sub>DS</sub> =300µA            | 1 – 2 | 650             | _    | -    | v                       | STR-Y6753 /<br>54                          |           |           |
| Voltage  |                             |                                   |       | 800             | _    | _    |                         | STR-Y6763 /<br>63A / 65 /66<br>/66A        |           |           |
| Drain Leakage Current                              | I <sub>DSS</sub>            | V <sub>DS</sub> =V <sub>DSS</sub> | 1 – 2 | -               | _    | 300  | μΑ                      |  |           |           |
|  |                             |                                   |       | _               |      | 0.8  |                         | STR-Y6735<br>/ 35A                         |           |           |
|  |                             |                                   |       | _               | _    | 1.4  |                         | STR-Y6754                                  |           |           |
| On Resistance                                      | D                           |                                   | 1 – 2 | -               |      | 1.7  | Ω                       | STR-Y6766<br>/ 66A                         |           |           |
| On Resistance                                      | R <sub>DS(ON)</sub>         |                                   |       |                 |      | 1.9  |                         | STR-Y6753                                  |           |           |
|  |                             |                                   |       |                 |      | 2.2  |                         | STR-Y6765                                  |           |           |
|  |                             |                                   |       | _               | -    | 3.5  |                         | STR-Y6763<br>/ 63A                         |           |           |
|  |                             |                                   |       | -               | -    | 250  | ns                      | STR-Y6753<br>/ 63 / 63A                    |           |           |
| Switching Time                                     | t <sub>f</sub>              |                                   | 1 – 2 | _               |      | 300  | ns                      | STR-Y6735<br>/ 35A / 54 /<br>66 / 66A / 65 |           |           |
| Thermal Resistance                                 |                             |                                   |       |                 |      |      |                         |  |           |           |
|  |                             |                                   |       | _               | 2.4  | 2.7  |                         | STR-Y6735<br>/ 35A / 54                    |           |           |
|  |                             |                                   |       | _               | 1.9  | 2.2  |                         | STR-Y6766<br>/ 66A                         |           |           |
| Channel to Frame Thermal Resistance <sup>(3)</sup> | $\theta_{ch-F}$             |                                   | _     | _               | 2.7  | 3.1  | °C/W                    | STR-Y6753                                  |           |           |
|  |                             |                                   |       |                 | -    | 2.3  | 2.6                     |  | STR-Y6765 |           |
|  |                             |                                   | _     | 2.8             | 3.2  |      | STR-Y6763<br>/ 63A      |  |           |           |
|  |                             |                                   | _     | 5.1             | 5.9  |      | STR-Y6735<br>/ 35A / 54 |  |           |           |
|  |                             |                                   |       | _               | 4.6  | 5.3  |                         | STR-Y6766<br>/ 66A                         |           |           |
| Channel to Case Thermal Resistance <sup>(4)</sup>  | ase Thermal $\theta_{ch-C}$ | $\theta_{ch-C}$ -                 |       | $\theta_{ch-C}$ | —    | _    | 5.4                     | 6.2  | °C/W      | STR-Y6753 |
|  |                             |                                   |       | _               | 5.0  | 5.8  |                         | STR-Y6765                                  |           |           |
|  |                             |                                   |       | _               | 5.5  | 6.3  |                         | STR-Y6763<br>/ 63A                         |           |           |

 $^{(3)} \theta_{ch-F}$  is thermal resistance between channel and internal frame.  $^{(4)} \theta_{ch-C}$  is thermal resistance between channel and case. Case temperature is measured at the backside surface.

# 3. Performance Curves

# 3.1 Derating Curves

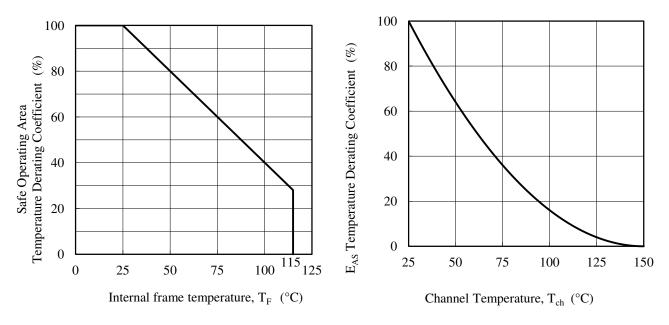
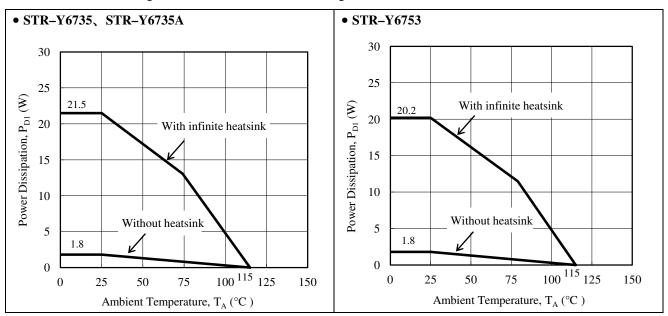
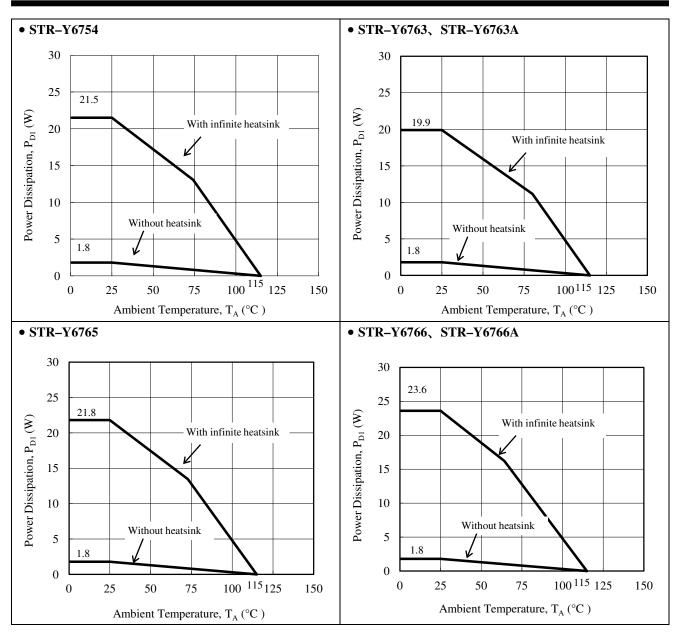


Figure 3-1 SOA Temperature Derating Coefficient Curve

Figure 3-2 Avalanche Energy Derating Coefficient Curve

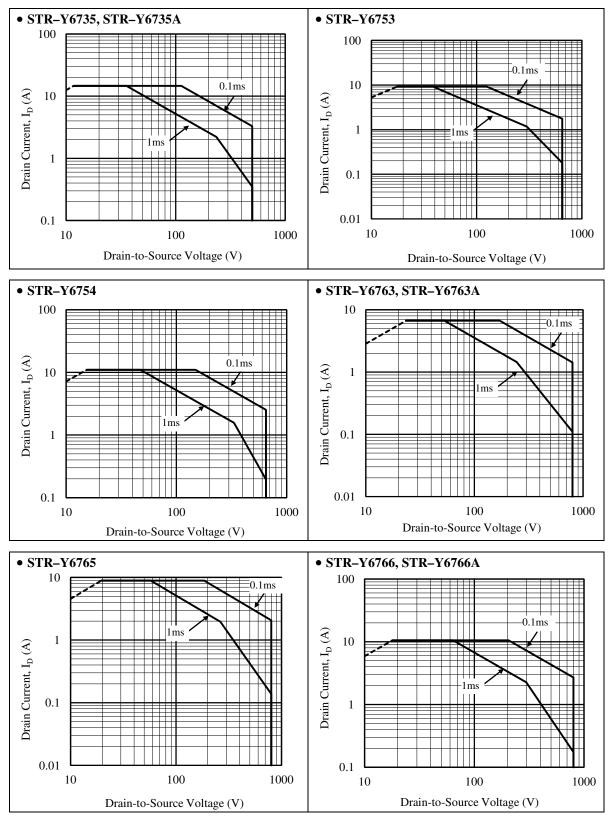


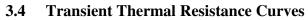
3.2 Ambient Temperature versus Power Dissipation Curves

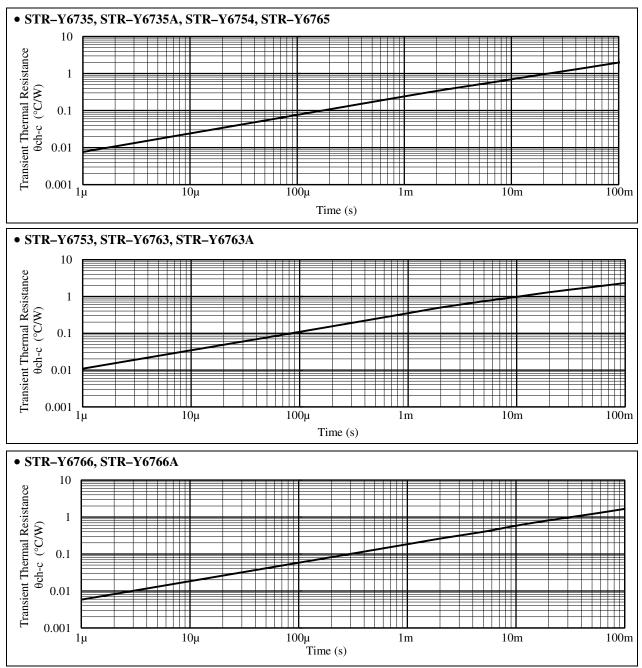


## 3.3 MOSFET Safe Operating Area Curves

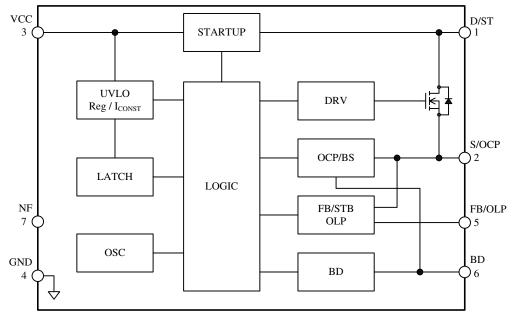
- When the IC is used, the safe operating area curve should be multiplied by the temperature derating coefficient derived from Figure 3-1.
- The broken line in the safe operating area curve is the drain current curve limited by on-resistance.
- Unless otherwise specified,  $T_A = 25$  °C, Single pulse







# 4. Block Diagram



BD\_STR-Y6700\_R1

# 5. Pin Configuration Definitions

|          | Pin | Name   | Descriptions   |  |  |  |  |
|----------|-----|--|--|--|--|--|--|
| 1 D/ST   | 1   | D/ST   | MOSFET drain and startup current input   |  |  |  |  |
| 2 S/OCP  | 2   | S/OCP MOSFET source and overcurrent protectio<br>(OCP) signal input                  |  |  |  |  |  |
| GND      | 3   | 3 VCC Power supply voltage input for contro<br>overvoltage protection (OVP) signal i |  |  |  |  |  |
| 6 BD     | 4   | GND  | Ground   |  |  |  |  |
| 17] NF   | 5   | FB/OLP   | Constant voltage control signal input and over<br>load protection (OLP) signal input |  |  |  |  |
| (LF3051) | 6   | BD   | Bottom Detection signal input, Input<br>Compensation detection signal input          |  |  |  |  |
|          | 7   | NF*  | (Non-function)   |  |  |  |  |

\*For stable operation, NF pin should be connected to GND pin, using the shortest possible path.

# 6. Typical Application

- The PCB traces D/ST pins should be as wide as possible, in order to enhance thermal dissipation.
- In applications having a power supply specified such that D/ST pin has large transient surge voltages, a clamp snubber circuit of a capacitor-resistor-diode (CRD) combination should be added on the primary winding P, or a damper snubber circuit of a capacitor (C) or a resistor-capacitor (RC) combination should be added between the D/ST pin and the S/OCP pin.
- For stable operation, NF pin should be connected to GND pin, using the shortest possible path.

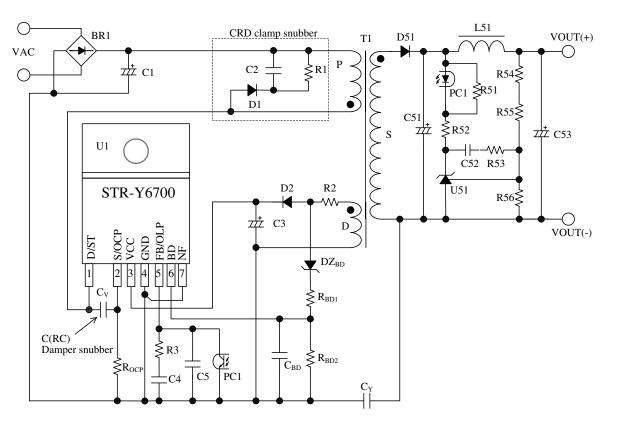
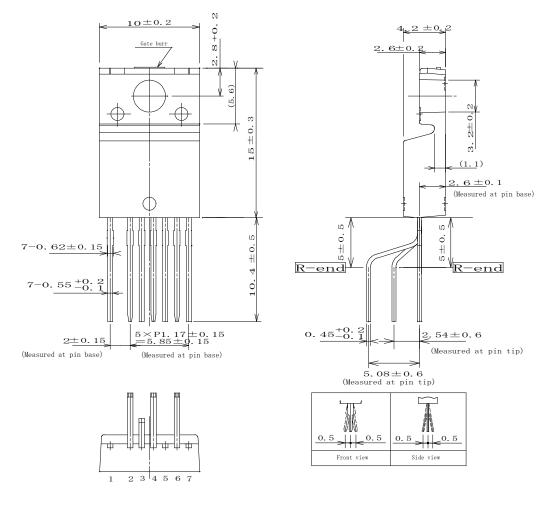


Figure 6-1 Typical application

# 7. Physical Dimensions

• TO220F-7L

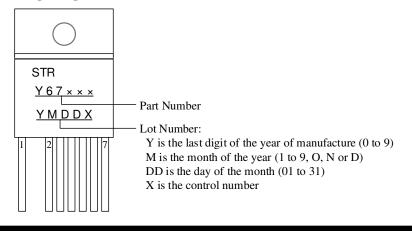


#### NOTES :

1) Dimension is in millimeters.

- 2) Leadform: LF No.3051
- 3) Gate burr indicates protrusion of 0.3 mm (max.).
- 4) Pin treatment Pb-free. Device composition compliant with the RoHS directive.

# 8. Marking Diagram



#### 9. Operational Description

- All of the parameter values used in these descriptions are typical values, unless they are specified as minimum or maximum.
- With regard to current direction, "+" indicates sink current (toward the IC) and "-" indicates source current (from the IC).

## 9.1 Startup Operation

Figure 9-1 shows the circuit around IC. Figure 9-2 shows the start up operation.

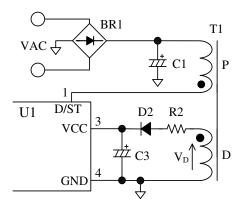


Figure 9-1 VCC pin peripheral circuit

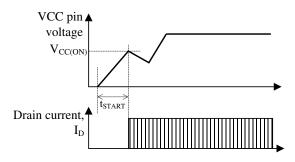


Figure 9-2 Startup operation

The IC incorporates the startup circuit. The circuit is connected to D/ST pin. When D/ST pin voltage reaches to Startup Circuit Operation Voltage  $V_{\text{START(ON)}} = 57 \text{ V}$ , the startup circuit starts operation.

During the startup process, the constant current,  $I_{CC(STARTUP)} = -3.1$  mA, charges C3 at VCC pin. When VCC pin voltage increases to  $V_{CC(ON)} = 15.1$  V, the control circuit starts operation. During the IC operation, the voltage rectified the auxiliary winding voltage,  $V_D$ , of Figure 9-1 becomes a power source to the VCC pin. After switching operation begins, the startup circuit turns off automatically so that its current consumption becomes zero.

The approximate value of auxiliary winding voltage is about 20 V, taking account of the winding turns of D

winding so that VCC pin voltage becomes Equation (1) within the specification of input and output voltage variation of power supply.

 $V_{CC(BIAS)}(max.) < V_{CC} < V_{CC(OVP)}(min.)$ 

$$\Rightarrow 12.5 \text{ (V)} < V_{\rm CC} < 28.5 \text{ (V)}$$
(1)

The startup time of IC is determined by C3 capacitor value. The approximate startup time  $t_{START}$  (shown in Figure 9-2) is calculated as follows:

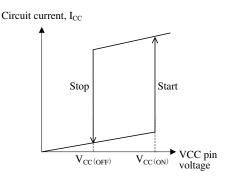
$$t_{\text{START}} = C3 \times \frac{V_{\text{CC(ON)}} - V_{\text{CC(INT)}}}{\left| I_{\text{CC(STRATUP)}} \right|}$$
(2)

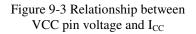
where,

 $\begin{array}{l} t_{START} & : \mbox{Startup time of IC (s)} \\ V_{CC(INT)} & : \mbox{Initial voltage on VCC pin (V)} \end{array}$ 

## 9.2 Undervoltage Lockout (UVLO)

Figure 9-3 shows the relationship of VCC pin voltage and circuit current  $I_{CC}$ . When VCC pin voltage decreases to  $V_{CC(OFF)} = 9.4$  V, the control circuit stops operation by Undervoltage Lockout (UVLO) circuit, and reverts to the state before startup.





#### 9.3 Bias Assist Function

By the Bias Assist Function, the startup failure is prevented and the latched state is kept.

The Bias Assist function is activated, when the VCC voltage decreases to the Startup Current Biasing Threshold Voltage,  $V_{CC(BIAS)} = 11.0$  V, in either of following condition:

the FB pin voltage is the Standby Operation Threshold Voltage,  $V_{FB(STBOP)} = 0.80$  V or less

or the IC is in the latched state due to activating the protection function.

When the Bias Assist Function is activated, the VCC pin voltage is kept almost constant voltage,  $V_{CC(BIAS)}$  by providing the startup current,  $I_{STARTUP}$ , from the startup circuit. Thus, the VCC pin voltage is kept more than  $V_{CC(OFF)}$ .

Since the startup failure is prevented by the Bias Assist Function, the value of C3 connected to VCC pin can be small. Thus, the startup time and the response time of the OVP become shorter.

The operation of the Bias Assist Function in startup is as follows. It is necessary to check and adjust the startup process based on actual operation in the application, so that poor starting conditions may be avoided.

Figure 9-4 shows VCC pin voltage behavior during the startup period.

After VCC pin voltage increases to  $V_{CC(ON)} = 15.1 \text{ V}$  at startup, the IC starts the operation. Then circuit current increases and VCC pin voltage decreases. At the same time, the auxiliary winding voltage  $V_D$  increases in proportion to output voltage. These are all balanced to produce VCC pin voltage.

When VCC pin voltage is decrease to  $V_{CC(OFF)} = 9.4 \text{ V}$  in startup operation, the IC stops switching operation and a startup failure occurs.

When the output load is light at startup, the output voltage may become more than the target voltage due to the delay of feedback circuit. In this case, the FB pin voltage is decreased by the feedback control. When the FB pin voltage decreases to the Standby Operation Threshold Voltage,  $V_{FB(STBOP)} = 0.80$  V, or less, the IC stops switching operation and VCC pin voltage decreases. When VCC pin voltage decreases to  $V_{CC(BIAS)}$ , the Bias Assist function is activated and the startup failure is prevented.

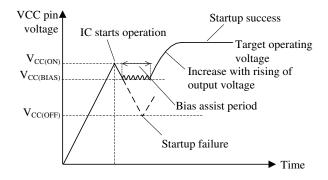


Figure 9-4 VCC pin voltage during startup period

#### 9.4 Soft Start Function

Figure 9-5 shows the behavior of VCC pin voltage, drain current and BD pin voltage during the startup period.

The IC activates the soft start circuitry during the startup period. Soft start is fixed to  $t_{SS} = 6.05$  ms. During the soft start period, over current threshold is increased

step-wisely (4 steps). This function reduces the voltage and the current stress of MOSFET and secondary side rectifier diode.

During the soft start operation period, the operation is in PWM operation, at an internally set operation frequency,  $f_{OSC} = 21.0$  kHz.

Until BD pin voltage becomes the following condition after the soft start time, the switching operation is PWM control of  $f_{OSC} = 21.0$  kHz.

When BD pin voltage,  $V_{BD}$ , becomes the following condition, the IC starts quasi-resonant operation.

Quasi-resonant operation starting condition

- $V_{BD} \ge V_{BD(TH1)} = 0.24 V$
- The effective pulse width of quasi-resonant signal is 1.0 µs or more (refer to Figure 9-12)

After the soft start period, D/ST pin current,  $I_D$ , is limited by the overcurrent protection (OCP), until the output voltage increases to the target operating voltage. This period is given as  $t_{LIM}$ .

When  $t_{LIM}$  is longer than the OLP Delay Time,  $t_{OLP}$ , the output power is limited by the OLP operation (OLP).

Thus, the  $t_{OLP}$  must be set longer than  $t_{LIM}$  (refer to Section 9.13).

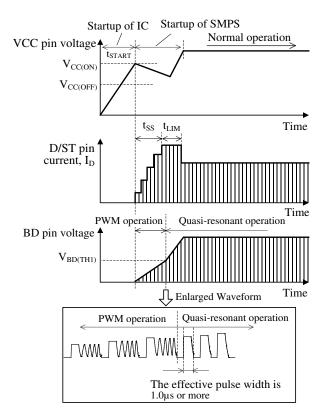


Figure 9-5  $V_{CC}$  and  $I_D$  and  $V_{BD}$  behavior during startup

#### 9.5 Constant Output Voltage Control

The IC achieves the constant voltage control of the power supply output by using the current-mode control method, which enhances the response speed and provides the stable operation.

The IC compares the voltage,  $V_{ROCP}$ , of a current detection resistor with the target voltage,  $V_{SC}$ , by the internal FB comparator, and controls the peak value of  $V_{ROCP}$  so that it gets close to  $V_{SC}$ , as shown in Figure 9-6 and Figure 9-7.  $V_{SC}$  is generated by the FB/OLP pin voltage.

• Light load conditions

When load conditions become lighter, the output voltage,  $V_{OUT}$ , increases. Thus, the feedback current from the error amplifier on the secondary-side also increases. The feedback current is sunk at the FB/OLP pin, transferred through a photo-coupler, PC1, and the FB/OLP pin voltage decreases. Thus,  $V_{SC}$  decreases, and the peak value of  $V_{ROCP}$  is controlled to be low, and the peak drain current of  $I_D$  decreases.

This control prevents the output voltage from increasing.

• Heavy load conditions

When load conditions become greater, the IC performs the inverse operation to that described above. Thus,  $V_{SC}$  increases and the peak drain current of  $I_D$  increases.

This control prevents the output voltage from decreasing.

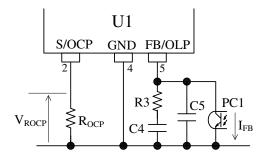


Figure 9-6 FB/OLP pin peripheral circuit

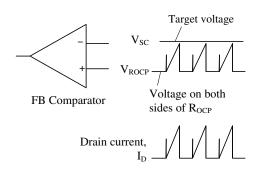


Figure 9-7 Drain current, I<sub>D</sub>, and FB comparator operation in steady operation

#### 9.6 Leading Edge Blanking Function

The IC uses the peak-current-mode control method for the constant voltage control of output.

In peak-current-mode control method, there is a case that the power MOSFET turns off due to unexpected response of FB comparator or overcurrent protection circuit (OCP) to the steep surge current in turning on a power MOSFET.

In order to prevent this response to the surge voltage in turning-on the power MOSFET, the Leading Edge Blanking,  $t_{ON(LEB)}$  is built-in. During  $t_{ON(LEB)}$ , the OCP threshold voltage becomes  $V_{OCP(La.OFF)} = 1.83$  V in order not to respond to the turn-on drain current surge (refer to Section 9.12).

# 9.7 Quasi-Resonant Operation and Bottom-On Timing Setup

#### 9.7.1 Quasi-Resonant Operation

Using quasi-resonant operation, switching loss and switching noise are reduced and it is possible to obtain converters with high efficiency and low noise. This IC performs quasi-resonant operation during one bottom-skip operation.

Figure 9-8 shows the circuit of a flyback converter. The meaning of symbols in Figure 9-8 is shown in Table 9-1. A flyback converter is a system that transfers the energy stored in the transformer to the secondary side when the primary side power MOSFET is turned off. After the energy is completely transferred to the secondary, when the power MOSFET keeps turning off, the  $V_{DS}$  begins free oscillation based on the L<sub>P</sub> and C<sub>V</sub>.

The quasi-resonant operation is the bottom-on operation that the power MOSFET turns-on at the bottom point of free oscillation of  $V_{DS}$ .

Figure 9-9 shows an ideal  $V_{DS}$  waveform during bottom-on operation.

The delay time,  $t_{ONDLY}$ , is the time from starting free oscillation of  $V_{DS}$  to power MOSFET turn-on. The  $t_{ONDLY}$  of an ideal bottom-on operation is half cycle of the free oscillation, and is calculated using Equation (3).

$$t_{ONDLY} \doteq \pi \sqrt{L_P \times C_V} \tag{3}$$

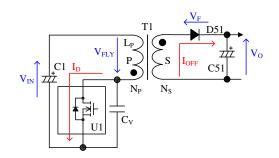


Figure 9-8 Basic flyback converter circuit

| Symbol           | Descriptions  |
|------------------|---|
|                  | *   |
| V <sub>IN</sub>  | Input voltage   |
| V <sub>FLY</sub> | Flyback voltage   |
|                  | $\mathbf{V}_{\mathrm{FLY}} = \frac{\mathbf{N}_{\mathrm{P}}}{\mathbf{N}_{\mathrm{S}}} \times \left(\mathbf{V}_{\mathrm{O}} + \mathbf{V}_{\mathrm{F}}\right)$ |
| V <sub>DS</sub>  | The voltage between Drain and Source of   |
|                  | power MOSFET  |
| N <sub>P</sub>   | Primary side number of turns  |
| Ns               | Secondary side number of turns  |
| Vo               | Output voltage  |
| V <sub>F</sub>   | Forward voltage drop of the secondary   |
|                  | side rectifier  |
| ID               | Drain current of power MOSFET   |
| I <sub>OFF</sub> | Current which flows through the   |
|                  | secondary side rectifier when power   |
|                  | MOSFET is off   |
| Cv               | Voltage resonant capacitor  |
| L <sub>P</sub>   | Primary side inductance   |

Table 9-1 The meaning of symbols in Figure 9-8

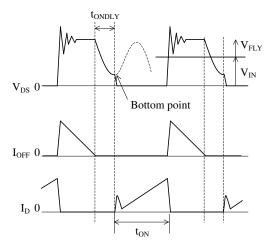


Figure 9-9 Ideal bottom-on operation waveform

#### 9.7.2 Bottom-On Timing Setup

BD pin detects the signal of bottom-on timing and input compensation of OCP1 (refer to Section 9.12.3). Figure 9-10 shows the BD pin peripheral circuit, Figure 9-11 shows the waveform of auxiliary winding voltage.

The quasi-resonant signal,  $V_{REV2}$ , is proportional to auxiliary winding voltage,  $V_D$  and is calculated as follows:

$$V_{\text{REV2}} = \frac{R_{\text{BD2}}}{R_{\text{BD1}} + R_{\text{BD2}}} \times \left(V_{\text{REV1}} - V_{\text{F}}\right)$$
(4)

where,

 $V_{REV1}$ : Flyback voltage of auxiliary winding D  $V_F$ : Forward voltage drop of  $Z_{BD}$ 

The BD pin detects the bottom point using the  $V_{\text{REV2}}.$ 

The threshold voltage of quasi-resonant operation has a hysteresis.  $V_{BD(TH1)}$  is Quasi-Resonant Operation Threshold Voltage 1,  $V_{BD(TH2)}$  is Quasi-Resonant Operation Threshold Voltage 2.

When the BD pin voltage,  $V_{REV2}$ , increases to  $V_{BD(TH1)} = 0.24$  V or more at the power MOSFET turns-off, the power MOSFET keeps the off-state. After that, the  $V_{DS}$  decreases by the free oscillation. When the  $V_{DS}$  decreases to  $V_{BD(TH2)} = 0.17$  V, the power MOSFET turns-on and the threshold voltage goes up to  $V_{BD(TH1)}$  automatically to prevent malfunction of the BD pin from noise interference.

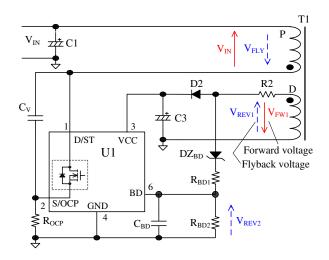


Figure 9-10 BD pin peripheral circuit

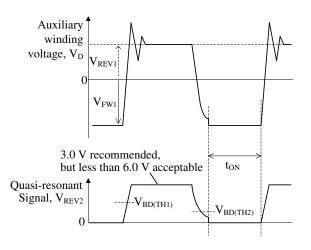


Figure 9-11 The waveform of auxiliary winding voltage

•  $R_{BD1}$  and  $R_{BD2}$  Setup  $R_{BD1}$  and  $R_{BD2}$  should be set so that  $V_{REV2}$  becomes the following range:

Under the lowest condition of VCC pin voltage in power supply specification,  $V_{REV2} \ge V_{BD(TH1)} = 0.34$  V(max.).

Under the highest condition of VCC pin voltage in

power supply specification,  $V_{REV2} < 6.0$  V (Absolute maximum rating of the BD pin) and the effective pulse width of quasi-resonant signal is 1.0 µs or more (refer to Figure 9-12).

The value of  $V_{REV2}$  is recommended about 3.0 V.

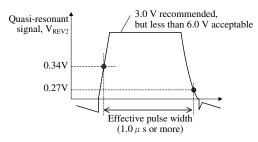


Figure 9-12 The effective pulse width of quasi-resonant signal

• C<sub>BD</sub> Setup

The delay time,  $t_{ONDLY}$ , until which the power MOSFET turns on, is adjusted by the value of  $C_{BD}$ , so that the power MOSFET turns on at the bottom-on of  $V_{DS}$  (refer to Figure 9-9).

The initial value of  $C_{BD}$  is set about 1000 pF.  $C_{BD}$  is adjusted while observing the actual operation waveforms of  $V_{DS}$  and  $I_D$  under the maximum input voltage and the maximum output power (If a voltage probe is connected to BD pin, the bottom point may misalign).

If the turn-on point precedes the bottom of the  $V_{DS}$  signal (see Figure 9-13), after confirming the initial turn-on point, delay the turn-on point by increasing the  $C_{BD}$  value gradually, so that the turn-on will match the bottom point of  $V_{DS}$ .

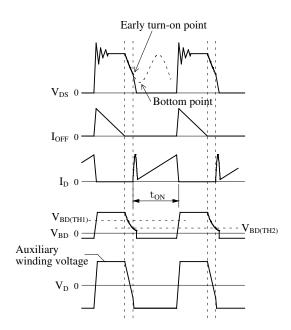


Figure 9-13 When the turn-on of a  $V_{DS}$  waveform occurs before a bottom point

In the converse situation, if the turn-on point lags behind the  $V_{DS}$  bottom point (Figure 9-14), after confirming the initial turn-on point, advance the turn-on point by decreasing the  $C_{BD}$  value gradually, so that the turn-on will match the bottom point of  $V_{DS}$ .

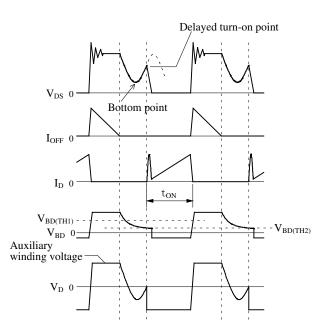


Figure 9-14 When the turn-on of a  $V_{\text{DS}}$  waveform occurs after a bottom point

# 9.8 BD Pin Blanking Time

Since the auxiliary winding voltage is input to the BD pin, BD pin voltage may be affected from the surge voltage ringing when the power MOSFET turns off. If the IC detects the surge voltage as quasi-resonant signal, the IC may repeatedly turn the power MOSFET on and off at high frequency. This result in an increase of the MOSFET power dissipation and temperature, and it can be damaged.

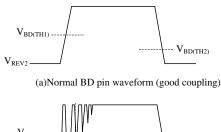
The BD pin has a blanking period of 250 ns (max.) to avoid detecting voltage during this period.

The poor coupling (the high leakage inductance) tends to happen in a low output voltage transformer design with high  $N_P/N_S$  turns ratio ( $N_P$  and  $N_S$  indicate the number of turns of the primary winding and secondary winding, respectively), and the surge voltage ringing of BD pin occurs easily (see Figure 9-15).

If the surge voltage continues longer than BD pin blanking period and the high frequency operation of power MOSFET occurs, the following adjustments are required so that the surge period of BD pin is less than 250 ns.

In addition, the BD pin waveform during operation should be measured by connecting test probes as short to the BD pin and the GND pin as possible, in order to measure any surge voltage correctly.

- $C_{BD}$  must be connected near the BD pin and the GND pin.
- The circuit trace loop between the BD pin and the GND pin must be separated from any traces carrying high current
- The coupling of the primary winding and the auxiliary winding must be good
- The clamping snubber circuit (refer to Figure 6-1) must be adjusted properly.





(b)Inappropriate BD pin waveform (poor coupling)

Figure 9-15 The difference of BD pin voltage,  $V_{REV2}$ , waveform by the coupling condition of the transformer

# 9.9 Multi-mode Control

When the output power decreases, the usual quasi-resonant control increases the switching frequency and the switching loss.

Thus, The IC has the multi-mode control to achieve high efficiency operation across the full range of loads.

The automatic multi-mode control changes among the following three operational modes according to the output loading state: normal quasi-resonant operation in heavy load, one bottom-skip quasi-resonant operation in medium to light load, and burst oscillation operation (auto standby function) in light load.

# 9.9.1 One Bottom-Skip Quasi-Resonant Operation

The one bottom-skip function limits the rise of the power MOSFET operation frequency in medium to light load in order to reduce the switching loss.

Figure 9-17 shows the operation state transition diagram of the output load from light load to heavy load. Figure 9-18 shows the state transition diagram from heavy load to light load.

As shown in Figure 9-16, in the process of the increase and decrease of load current, hysteresis is imposed at the time of each operational mode change. For this reason, the switching waveform does not become unstable near the threshold voltage of a change,

and this enables the IC to switch in a stable operation.

Before the one bottom-skip point changed from heavy to light load, or after that done from light to heavy load, the switching frequency of the normal quasi-resonant operation becomes higher and the switching loss of power MOSFET increases. Thus, the temperature of the power MOSFET should be checked at higher switching frequency of the operation changing point in maximum AC input voltage.

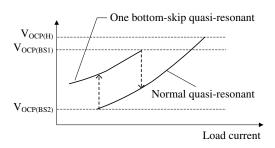


Figure 9-16 Hysteresis at the operational mode change

• The mode is changed from one bottom-skip quasi-resonant operation to normal quasi-resonant operation (light load to heavy load). When load is increased from one bottom-skip

when load is increased from one bottom-skip operation, the MOSFET peak drain current value will increase, and the positive pulse width will widen. Also, the peak value of the S/OCP pin voltage increases. When the load is increased further and the S/OCP pin voltage rises to  $V_{OCP(BS1)}$ , the mode is changed to normal quasi-resonant operation (see Figure 9-17).

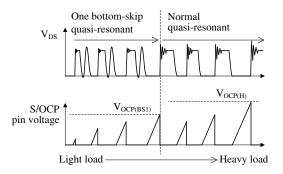


Figure 9-17 Operation state transition diagram from light load to heavy load conditions

• The mode is changed from normal quasi-resonant operation to one bottom-skip quasi-resonant operation (heavy load to light load).

When load is decreased from normal quasi-resonant operation, the MOSFET peak drain current value will decrease, and the positive pulse width will narrow. Also, the peak value of the S/OCP pin voltage decreases. When load is reduced further and the S/OCP pin voltage falls to  $V_{OCP(BS2)}$ , the mode is

changed to one bottom-skip quasi-resonant operation (see Figure 9-18).

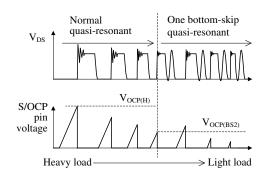


Figure 9-18 Operation state transition diagram from heavy load to light load conditions

Figure 9-19 shows the effective pulse width of normal quasi-resonant signal, and Figure 9-20 shows the effective pulse width of one bottom-skip quasi-resonant signal. In order to perform stable normal quasi-resonant operation and one bottom-skip operation, it is necessary to ensure that the pulse width of the quasi-resonant signal is 1  $\mu$ s or more under the conditions of minimum input voltage and minimum output power.

The pulse width of the quasi-resonant signal,  $V_{REV2}$ , is defined as the period from the maximum specification of  $V_{BD(TH1)}$ , 0.34 V, on the rising edge, to the maximum specification of  $V_{BD(TH2)}$ , 0.27 V on the falling edge of the pulse.

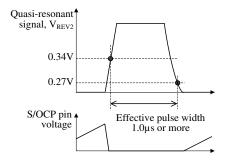
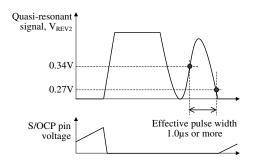
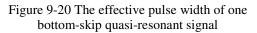


Figure 9-19 The effective pulse width of normal quasi-resonant signal





#### 9.9.2 Automatic Standby Mode Function

The S/OCP pin circuit monitors  $I_D$ . Automatic standby mode is activated automatically when  $I_D$  reduces under light load conditions at which the S/OCP pin voltage falls to the standby state threshold voltage (about 9% compared to  $V_{OCP(H)} = 0.910$  V).

During standby mode, when the FB/OLP pin voltage falls below  $V_{FB(STBOP)}$ , the IC stops switching operation, and the burst oscillation mode will begin, as shown in Figure 9-21.

Burst oscillation mode reduces switching losses and improves power supply efficiency because of periodic non-switching intervals.

Generally, to improve efficiency under light load conditions, the frequency of the burst oscillation mode becomes just a few kilohertz. Because the IC suppresses the peak drain current well during burst oscillation mode, audible noises can be reduced.

If the VCC pin voltage decreases to  $V_{CC(BIAS)} = 11.0 \text{ V}$ during the transition to the burst oscillation mode, the Bias Assist function is activated and stabilizes the Standby mode operation, because  $I_{CC(STARTUP)}$  is provided to the VCC pin so that the VCC pin voltage does not decrease to  $V_{CC(OFF)}$ .

However, if the Bias Assist function is always activated during steady-state operation including standby mode, the power loss increases. Therefore, the VCC pin voltage should be more than  $V_{CC(BIAS)}$ , for example, by adjusting the turns ratio of the auxiliary winding and secondary winding and/or reducing the value of R2 in Figure 10-2 (refer to Section 10.1 Peripheral Components for a detail of R2).

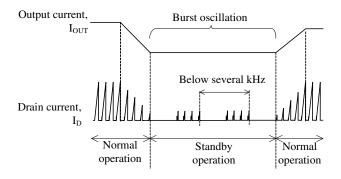


Figure 9-21 Auto Standby mode timing

#### 9.10 Maximum On-Time Limitation Function

When the input voltage is low or in a transient state such that the input voltage turns on or off, the on-time of the incorporated power MOSFET is limited to the maximum on-time,  $t_{ON(MAX)} = 40.0 \ \mu s$  in order to prevent the decreasing of switching frequency. Thus, the peak drain current is limited, and the audible noise of the transformer is suppressed.

In designing a power supply, the on-time must be less

than  $t_{ON(MAX)}$  (see Figure 9-22).

If such a transformer is used that the on-time is  $t_{ON(MAX)}$  or more, under the condition with the minimum input voltage and the maximum output power, the output power would become low. In that case, the transformer should be redesigned taking into consideration the following:

- Inductance, L<sub>P</sub>, of the transformer should be lowered in order to raise the operation frequency.
- Lower the primary and the secondary turns ratio,  $N_{\rm P}$  /  $N_{\rm S},$  to lower the duty cycle.

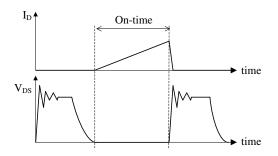


Figure 9-22 Confirmation of maximum on-time

#### 9.11 Overcurrent Protection (OCP)

The IC has an Overcurrent Protection 1 (OCP1) and an Overcurrent Protection 2 (OCP2).

OCP1 function: pulse-by-pulse, with Input Compensation Function. The OCP2 function: In case output winding is shorted etc., the IC stops switching operation at the latched state. The products with the last letter "A" don't have the OCP2 function.

#### **9.11.1** Overcurrent Protection 1 (OCP1)

OCP1 detects each drain peak current level of a power MOSFET on pulse-by-pulse basis, and limits the output power when the current level reaches to OCP threshold voltage. During Leading Edge Blanking Time ( $t_{BW}$ ), OCP1 is disabled. When power MOSFET turns on, the surge voltage width of S/OCP pin should be less than  $t_{ON(LEB)}$ , as shown in Figure 9-23. In order to prevent surge voltage, pay extra attention to  $R_{OCP}$  trace layout (refer to Section 10.3).

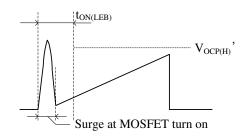


Figure 9-23 S/OCP pin voltage

In addition, if a C (RC) damper snubber of Figure 9-24 is used, reduce the capacitor value of damper snubber. If the turn-on timing isn't fitted to a VDs bottom point, adjustments are required (refer to Section 9.7.2).

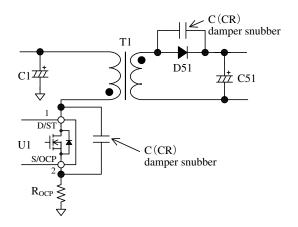


Figure 9-24 Damper snubber circuit

#### 9.11.2 Overcurrent Protection 2 (OCP2)

The products with the last letter "A" don't have the OCP2 function.

As the protection for an abnormal state, such as an output winding being shorted or the withstand voltage of secondary rectifier being out of specification, when the S/OCP pin voltage reaches  $V_{OCP(La.OFF)} = 1.83$  V, the IC stops switching operation immediately, in latch mode.

This overcurrent protection also operates during the leading edge blanking.

Releasing the latched state is done by turning off the input voltage and by dropping the VCC pin voltage below  $V_{CC(OFF)}$ .

#### 9.11.3 OCP1 Input Compensation Function

The usual control ICs have some propagation delay time. The steeper the slope of the actual drain current at a high AC input voltage is, the larger the detection voltage of actual drain peak current is, compared to overcurrent detection threshold voltage. Thus, the peak current has some variation depending on the AC input voltage in OCP1 state.

When using a quasi-resonant converter with universal input (85 to 265 VAC), if the output power is set constant, then because higher input voltages have higher frequency, the on-time is reduced. Thus, the peak current in OCP1 state tends to be affected by propagation delay in the higher input voltage.

If the IC does not have Input Compensation Function, the output current at OCP1 point in the maximum input voltage,  $I_{OUT(OCP)}$ , becomes about double of  $I_{OUT}$  (Figure 9-25 "without input compensation").  $I_{OUT}$  is the target output current considered with maximum output power in the minimum input voltage.

In order to suppress this variability, this IC has the overcurrent input compensation function.

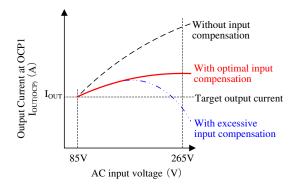


Figure 9-25 OCP1 input compensation

Figure 9-26 shows the OCP1 input compensation circuit. The value of input compensation is set by BD pin peripheral circuit.

By OCP1 Input Compensation Function, Overcurrent Detection 1 Threshold Voltage in Normal Operation,  $V_{OCP(H)} = 0.910$  V, is compensated depending on an AC input voltage.

The forward voltage of auxiliary winding D,  $V_{FW1}$ , is proportional to AC input voltage. As shown in Figure 9-26, the voltage obtained by subtracting zener voltage,  $V_Z$ , of  $DZ_{BD}$  from  $V_{FW1}$  is biased by either end of  $R_{BD1}$ and  $R_{BD2}$ , and thus the BD pin voltage is provided the voltage on  $R_{DB2}$  divided by the divider of  $R_{BD1}$  and  $R_{BD2}$ .

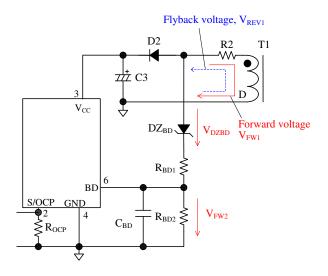


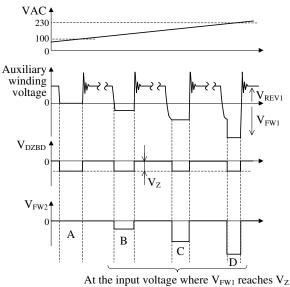
Figure 9-26 OCP input compensation circuit

Figure 9-27 shows the each voltage waveform for the input voltage in normal quasi-resonant operation.

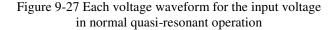
When  $V_{\text{DZBD}} \geq V_{FW1}$  (Point A), No input compensation required,  $V_{FW2}$  remains zero, and the detection voltage for an overcurrent event is the Overcurrent 1 Detection Threshold Voltage in Normal Operation,  $V_{\text{OCP(H)}}$ .

When  $V_{DZBD} < V_{FW1}$  (Point B through Point D), the input voltage is increased and  $V_{FW1}$  exceeds the Zener voltage,  $V_Z$ , of  $DZ_{BD}$ .  $V_{FW2}$  will be produced as a negative voltage to compensate  $V_{OCP(H)}$ .

The value of  $V_{FW2}$  should be adjusted so that the difference between  $I_{OUT}$  and  $I_{OUT(OCP)}$  is minimized as shown in Figure 9-25 "With optimal input compensation". If the excessive input compensation,  $I_{OUT(OCP)}$  may become less than  $I_{OUT}$  (Figure 9-25 "With excessive input compensation"). Thus, value of  $V_{FW2}$  must be adjusted so that  $I_{OUT(OCP)}$  remains more than  $I_{OUT}$ , across the input voltage range.



or more, V<sub>FW2</sub> goes negative.



Setup of BD pin peripheral components (DZ<sub>BD</sub>,  $R_{BD1}$  and  $R_{BD2}$ ) is as follows:

1) V<sub>IN(AC)C</sub> Setup

 $V_{IN(AC)C}$  is the AC input voltage that starts input compensation. In general specification,  $V_{IN(AC)C}$  is set 120 VAC to 170 VAC.

2) V<sub>Z</sub> Setup

 $V_{IN(AC)C}$  is adjusted by the zener voltage,  $V_Z$ , of  $DZ_{BD}$ . The  $V_{FW1}$  at  $V_{IN(AC)C}$  is calculated by using Equation (5).  $V_Z$  is set from the result.

$$V_{FW1} = \frac{N_D}{N_P} \times V_{IN(AC)C} \times \sqrt{2} = V_Z$$
(5)

where, N<sub>P</sub>: Primary side number of turns N<sub>D</sub>: Secondary side number of turns

3)  $R_{BD1}$  and  $R_{BD2}$  Setup.

The recommended value of  $R_{BD2}$  is 1.0 k $\Omega$ . In general specification,  $R_{BD1}$  is set by using result of Equation (6) so that  $V_{FW2} = -3.0$  V at maximum AC input voltage.

$$R_{BD1} = \frac{R_{BD2}}{|V_{FW2}|} \times \left( \frac{N_D}{N_P} \times V_{IN(AC)MAX} \times \sqrt{2} - V_Z - |V_{FW2}| \right)$$
(6)

where,

 $\begin{array}{l} V_{FW2} : BD \ pin \ voltage \ (-3.0 \ V) \\ N_P : Primary \ side \ winding \ number \ of \ turns \\ N_D : \ Auxiliary \ winding \ number \ of \ turns \\ V_{IN(AC)MAX} : \ Maximum \ AC \ input \ voltage \\ V_Z : \ Zener \ voltage \ of \ DZ_{BD} \end{array}$ 

4) V<sub>OCP(H)</sub>' is the overcurrent threshold voltage after input compensation. Figure 9-28 shows a relationship of V<sub>OCP(H)</sub>' and BD pin voltage, V<sub>FW2</sub>. V<sub>FW2</sub> at maximum AC input voltage is calculated by using Equation (7). V<sub>OCP(H)</sub>' and this variation are gotten by using the result from Figure 9-28. When V<sub>OCP(H)</sub>' including variation becomes the Bottom-Skip Operation Threshold Voltage 1, V<sub>OCP(BS1)</sub> = 0.572 V, or less, the operation of IC is one bottom-skip only and the output current may be less than target output current, I<sub>OUT</sub>.

$$\left| \mathbf{V}_{FW2} \right| = \frac{\mathbf{R}_{BD2}}{\mathbf{R}_{BD1} + \mathbf{R}_{BD2}} \times \left( \left| \mathbf{V}_{FW1} \right| - \mathbf{V}_{Z} \right)$$
$$= \frac{\mathbf{R}_{BD2}}{\mathbf{R}_{BD1} + \mathbf{R}_{BD2}} \times \left( \left| \frac{\mathbf{N}_{D}}{\mathbf{N}_{P}} \times \mathbf{V}_{IN(AC)MAX} \times \sqrt{2} \right| - \mathbf{V}_{Z} \right) \quad (7)$$

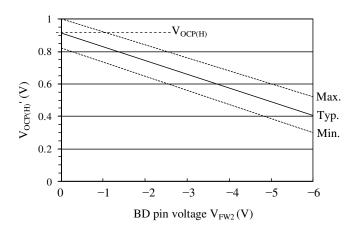


Figure 9-28 Overcurrent threshold voltage after input compensation,  $V_{OCP(H)}$ ' (reference for design target values)

5)  $V_{REV2}$  is calculated by using Equation (8) and is checked to be the Quasi-Resonant Operation Threshold Voltage 1,  $V_{BD(TH1)} = 0.34$  V (max.), or more (refer to Figure 9-11).

$$V_{REV2} = \frac{R_{BD2}}{R_{BD1} + R_{BD2}} \times (V_{REV1} - V_F) \ge 0.34 V$$
 (8)

where,

 $V_{REV1}$ : Flyback voltage of auxiliary wining  $V_F$ : Forward voltage drop of  $DZ_{BD}$ 

6) The BD pin voltage, which includes surge voltage, must be observed within the absolute maximum rating of the BD pin voltage (-6.0 to 6.0 V) in the actual operation at the maximum input voltage.

### < BD Pin Peripheral Components Value Selection Reference Example >

Setting value:

Input voltage:  $V_{IN(AC)} = 85$ VAC to 265VAC, AC input voltage that starts input compensation:  $V_{IN(AC)C} = 120$  VAC, Primary side winding number of turns:  $N_P = 40$  T, Auxiliary winding number of turns:  $N_D = 5$  T Forward voltage of auxiliary winding:  $V_{FW1} = 20$  V

 $V_{FW1}$  is calculated by using Equation (5) as follows:

$$V_{FW1} = \frac{N_D}{N_P} \times V_{IN(AC)C} \times \sqrt{2}$$
$$= \frac{5}{40} \times 120\sqrt{2} = 21.2V$$

Thus, zener voltage of  $DZ_{BD}$  is chosen to be 22 V of the E series.

When  $V_{FW2} = -3.0$  V at maximum input voltage, 265VAC,  $R_{BD1}$  is calculated by using Equation (6) as follows:

$$R_{BD1} = \frac{R_{BD2}}{|V_{FW2}|} \times \left(\frac{N_D}{N_P} \times V_{IN(AC)MAX} \times \sqrt{2} - V_Z - |V_{FW2}|\right)$$
$$= \frac{1k}{|-3|} \times \left(\frac{5}{40} \times 265\sqrt{2} - 22 - |-3|\right) = 7.28k \Omega$$

Thus,  $R_{BD1}$  is chosen to be 7.5 k $\Omega$  of the E series.

When  $R_{BD2} = 1.0 \text{ k}\Omega$ ,  $|V_{FW2}|$  value at 265 VAC is calculated by using Equation (7) as follows:

$$|\mathbf{V}_{FW2}| = \frac{\mathbf{R}_{BD2}}{\mathbf{R}_{BD1} + \mathbf{R}_{BD2}} \times (|\mathbf{V}_{FW1}| - \mathbf{V}_{Z})$$
$$= \frac{1k}{7.5k + 1k} \times (\frac{5}{40} \times 265\sqrt{2} - 22) = 2.92V$$

Referring to Figure 9-28, when  $V_{FW2}$  is compensated to -2.92 V, the overcurrent threshold voltage after input compensation,  $V_{OCP(H)}$ ', is set to about 0.66 V (typ).

When setting  $R_{BD2} = 1.0 \text{ k}\Omega$ ,  $R_{BD1} = 7.5 \text{ k}\Omega$ ,  $V_F = 0.7 \text{ V}$ , and  $V_{REV1} = 20 \text{ V}$ ,  $V_{REV2}$  is calculated by using Equation (8) as follows:

$$V_{\text{REV2}} = \frac{R_{\text{BD2}}}{R_{\text{BD1}} + R_{\text{BD2}}} \times (V_{\text{REV1}} - V_{\text{F}})$$
$$= \frac{1k}{1k + 7.5k} \times (20 - 0.7) = 2.27V$$

 $V_{\text{REV2}}$  is  $V_{\text{BD(TH1)}} = 0.34$  V (max.) or more.

# 9.11.4 When Overcurrent Input Compensation is Not Required

When the input voltage is narrow range, or provided from PFC circuit, the variation of the input voltage is small. Thus, the variation of OCP point may become less than that of the universal input voltage specification.

When overcurrent input compensation is not required, the input compensation function can be disabled by substituting a high-speed diode for the zener diode,  $DZ_{BD}$ , and by keeping BD pin voltage from being minus voltage. In addition, Equation (9) shows the reverse voltage of a high-speed diode. The peak reverse voltage of high-speed diode selection should take account of its derating.

$$V_{FW1} = \frac{N_D}{N_P} \times V_{IN(AC)MAX} \times \sqrt{2}$$
(9)

where,

 $\label{eq:VFW1} \begin{array}{l} V_{FW1} : \mbox{Forward voltage of auxiliary wining} \\ N_P : \mbox{Primary side number of turns} \\ N_D : \mbox{Secondary side number of turns} \\ V_{IN(AC)MAX} : \mbox{Maximum AC input voltage} \end{array}$ 

#### 9.12 Overload Protection (OLP)

Figure 9-29 shows the FB/OLP pin peripheral circuit, Figure 9-29 shows each waveform for Overload Protection (OLP) operation. When the peak drain current of  $I_{\rm D}$  is limited by Overcurrent Protection 1 operation, the output voltage,  $V_{\rm OUT}$ , decreases and the feedback current from the secondary photo-coupler becomes zero. Thus, the feedback current,  $I_{FB}$ , charges C4 connected to the FB/OLP pin and the FB/OLP pin voltage,  $V_{FB/OLP}$ , increases.

When  $V_{FB/OLP}$  increases to the FB Pin Maximum Voltage in Feedback Operation,  $V_{FB(MAX)} = 4.05$  V, or more, C4 is charged by  $I_{FB(OLP)} = -10 \mu$ A. When  $V_{FB/OLP}$ increases to the OLP Threshold Voltage,  $V_{FB(OLP)} = 5.96$ V, the OLP function is activated, the IC stops switching operation in the latched state. In order to keep the latched state, when VCC pin voltage decreases to  $V_{CC(BIAS)}$ , the bias assist function is activated and VCC pin voltage is kept to over the  $V_{CC(OFF)}$ .

Releasing the latched state is done by turning off the input voltage and by dropping the VCC pin voltage below  $V_{CC(OFF)}$ .

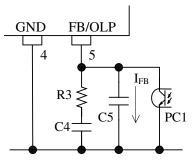


Figure 9-29 FB/OLP pin peripheral circuit

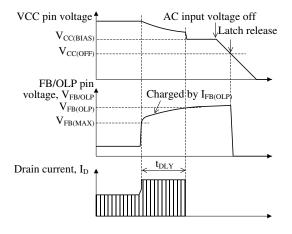


Figure 9-30 OLP operation waveforms

The time of the FB/OLP pin voltage from  $V_{FB(MAX)}$  to  $V_{FB(OLP)}$  is defined as the OLP delay time,  $t_{DLY}$ . Because the capacitor C5 for phase compensation is small compared to C4, the approximate value of  $t_{DLY}$  is calculated by Equation (10). When C4 = 4.7  $\mu$ F, the value of  $t_{DLY}$  would be approximately 0.9 s. The recommended value of R3 is 47 k $\Omega$ .

$$t_{DLY} \doteq \frac{\left(V_{FB(OLP)} - V_{FB(MAX)}\right) \times C4}{\left|I_{FB(OLP)}\right|}$$
$$t_{DLY} \doteq \frac{\left(5.96V - 4.05V\right) \times C4}{\left|-10\mu A\right|}$$
(10)

To enable the overload protection function to initiate an automatic restart, 220 k $\Omega$  is connected between the FB/OLP pin and ground, as a bypass path for I<sub>FB(OLP)</sub>, as shown in Figure 9-31. Thus, the FB/OLP pin is kept under V<sub>FB(OLP)</sub> in OLP state.

In OLP state as an output shorted, the output voltage and VCC pin voltage decrease. During the operation, Bias Assist Function is disabled. Thus, VCC pin voltage decreases to  $V_{CC(OFF)}$ , the control circuit stops operation. After that, the IC reverts to the initial state by UVLO circuit, and the IC starts operation when VCC pin voltage increases to  $V_{CC(ON)}$  by startup current. Thus the intermittent operation by UVLO is repeated in OLP state without latched operation as shown in Figure 9-32.

The intermittent oscillation is determined by the cycle of the charge and discharge of the capacitor C3 connected to the VCC pin. In this case, the charge time is determined by the startup current from the startup circuit, while the discharge time is determined by the current supply to the internal circuits of the IC.

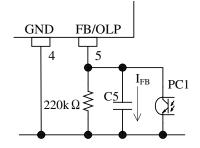


Figure 9-31 FB/OLP pin peripheral circuit (without latched operation)

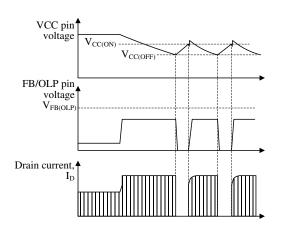


Figure 9-32 OLP operation waveform at output shorted (without latched operation)

# increases to $V_{CC(OVP)} = 31.5$ V or more, Overvoltage Protection (OVP) is activated, the IC stops switching

Protection (OVP) is activated, the IC stops switching operation at the latched state. In order to keep the latched state, when VCC pin voltage decreases to  $V_{CC(BIAS)}$ , the bias assist function is activated and VCC pin voltage is kept to over the  $V_{CC(OFF)}$ .

When a voltage between VCC pin and GND pin

9.13 Overvoltage Protection (OVP)

Releasing the latched state is done by turning off the input voltage and by dropping the VCC pin voltage below  $V_{\text{CC(OFF)}}.$ 

When the VCC pin voltage is provided by using auxiliary winding of transformer, the overvoltage conditions such as output voltage detection circuit open can be detected because the VCC pin voltage is proportional to output voltage. The approximate value of output voltage  $V_{OUT(OVP)}$  in OVP condition is calculated by using Equation (11).

$$V_{OUT(OVP)} = \frac{V_{OUT(NORMAL)}}{V_{CC(NORMAL)}} \times 31.5 \text{ (V)}$$
(11)

where,

 $V_{OUT(NORMAL)}$ : Output voltage in normal operation  $V_{CC(NORMAL)}$ : VCC pin voltage in normal operation

#### 9.14 Thermal Shutdown (TSD)

When the temperature of control circuit increases to  $T_{j(TSD)} = 135$  °C (min.) or more, Thermal Shutdown (TSD) is activated, the IC stops switching operation at the latched state. In order to keep the latched state, when VCC pin voltage decreases to  $V_{CC(BIAS)}$ , the bias assist function is activated and VCC pin voltage is kept to over the  $V_{CC(OFF)}$ .

# 10. Design Notes

# **10.1 External Components**

Take care to use properly rated, including derating as necessary and proper type of components.

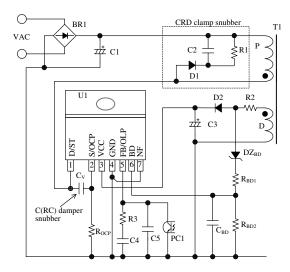


Figure 10-1 The IC peripheral circuit

#### • Input and Output Electrolytic Capacitor

Apply proper derating to ripple current, voltage, and temperature rise. Use of high ripple current and low impedance types, designed for switch mode power supplies, is recommended.

#### • S/OCP Pin Peripheral Circuit

In Figure 10-1,  $R_{OCP}$  is the resistor for the current detection. A high frequency switching current flows to  $R_{OCP}$ , and may cause poor operation if a high inductance resistor is used. Choose a low inductance and high surge-tolerant type.

#### • VCC Pin Peripheral Circuit

The value of C3 in Figure 10-1 is generally recommended to be  $10\mu$  to  $47\mu$ F (refer to Section 9.1 Startup Operation", because the startup time is determined by the value of C3).

In actual power supply circuits, there are cases in which the VCC pin voltage fluctuates in proportion to the output current,  $I_{OUT}$  (see Figure 10-2), and the Overvoltage Protection function (OVP) on the VCC pin may be activated. This happens because C3 is charged to a peak voltage on the auxiliary winding D, which is caused by the transient surge voltage coupled from the primary winding when the power MOSFET turns off.

For alleviating C3 peak charging, it is effective to add some value R2, of several tenths of ohms to several ohms, in series with D2 (see Figure 10-1). The optimal value of R2 should be determined using a transformer matching what will be used in the actual application, because the variation of the auxiliary winding voltage is affected by the transformer structural design.

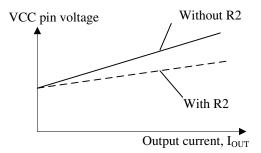


Figure 10-2 Variation of VCC pin voltage and power

#### • FB/OLP Pin Peripheral Circuit

C5 is for high frequency noise reduction and phase compensation, and should be connected close to these pins. The value of C5 is recommended to be about 470 pF to  $0.01\mu$ F, and should be selected based on actual operation in the application.

C4 is for the OLP delay time,  $t_{DLY}$ , setting (refer to Section 9.13).

The recommended value of R3 is 47 k $\Omega$ .

#### • BD Pin Peripheral Circuit

Since BD pin detects the signal of bottom-on timing and input compensation of OCP1, the values of BD pin peripheral components ( $DZ_{BD}$ ,  $R_{BD1}$ ,  $R_{BD2}$  and  $C_{BD}$ ) are considered about both functions and should be adjusted.

Refer to Section 9.7.2 and Section 9.12.3.

#### • NF Pin

For stable operation, NF pin should be connected to GND pin, using the shortest possible path.

#### • Snubber Circuit

When the surge voltage of  $V_{DS}$  is large, the circuit should be added as follows (see Figure 10-1);

- A clamp snubber circuit of a capacitor-resistordiode (CRD) combination should be added on the primary winding P.
- A damper snubber circuit of a capacitor (C) or a resistor-capacitor (RC) combination should be added between the D/ST pin and the S/OCP pin. When the damper snubber circuit is added, this components should be connected near D/ST pin and S/OCP pin.
- Peripheral Circuit of Secondary Side Shunt Regulator

Figure 10-3 shows the secondary side detection circuit with the standard shunt regulator IC (U51).